

EAST - [10650000.wsp:1]

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 L2: (8295) silicon adj controlled adj rectifier
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2 and (substrate and epitaxial and polysilicon)

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030122192 A1	20030703	22	Low-voltage-triggered SOI-SCR device and associated ESD protection circuit	257/347	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030047750 A1	20030313	21	Electrostatic discharge protection silicon controlled rectifier (ESD-SCR) for silicon	257/173	257/E29.211
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20030007301 A1	20030109	22	Low-voltage-triggered SOI-SCR device and associated ESD protection circuit	361/111	
12	<input type="checkbox"/>	<input type="checkbox"/>	US 20020180511 A1	20021205	10	Externally programmable antifuse	327/525	257/E23.147
13	<input type="checkbox"/>	<input type="checkbox"/>	US 6750515 B2	20040615	18	SCR devices in silicon-on-insulator CMOS process for on-chip ESD protection	257/357	257/338; 257/347;
14	<input type="checkbox"/>	<input type="checkbox"/>	US 6737682 B1	20040518	12	High voltage tolerant and low voltage triggering floating-well silicon controlled	257/173	257/347; 257/350;
15	<input type="checkbox"/>	<input type="checkbox"/>	US 6713818 B2	20040330	24	Electrostatic discharge protection device	257/362	257/355; 257/360
16	<input type="checkbox"/>	<input type="checkbox"/>	US 6642088 B1	20031104	18	Silicon-controlled rectifier structures on silicon-on insulator with shallow trench	438/155	438/480
17	<input type="checkbox"/>	<input type="checkbox"/>	US 6630377 B1	20031007	15	Method for making high-gain vertical bipolar junction transistor structures compatible	438/202	257/E21.375; 257/E21.696;
18	<input type="checkbox"/>	<input type="checkbox"/>	US 6624487 B1	20030923	16	Drain-extended MOS ESD protection structure	257/409	257/355; 257/410;
19	<input type="checkbox"/>	<input type="checkbox"/>	US 6576974 B1	20030610	23	Bipolar junction transistors for on-chip electrostatic discharge protection and	257/499	257/362; 257/526;